

AFRL-SN-WP-TM-2003-1191

**HEAT DISSIPATION FOR HIGH POWER
OPTICALLY PUMPED
SEMICONDUCTOR VERTICAL
EXTERNAL CAVITY SURFACE
EMITTING LASERS**



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OCTOBER 2003

Interim Report for 06 June 2003 – 15 October 2003

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STINFO FINAL REPORT

**SENSORS DIRECTORATE
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20040112 177

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151
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REPORT DOCUMENTATION PAGE					<i>Form Approved</i> OMB No. 0704-0188	
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1. REPORT DATE (DD-MM-YY) October 2003		2. REPORT TYPE Interim		3. DATES COVERED (From - To) 06/06/03 – 10/15/03		
4. TITLE AND SUBTITLE HEAT DISSIPATION FOR HIGH POWER OPTICALLY PUMPED SEMICONDUCTOR VERTICAL EXTERNAL CAVITY SURFACE EMITTING LASERS				5a. CONTRACT NUMBER IN-HOUSE		
				5b. GRANT NUMBER		
				5c. PROGRAM ELEMENT NUMBER 61102F		
6. AUTHOR(S) Thomas Nelson and Donald Agresta (AFRL/SNDD) James Ehret (AFRL/MLPSM)				5d. PROJECT NUMBER 2305		
				5e. TASK NUMBER DW		
				5f. WORK UNIT NUMBER 01		
7. PERFORMING ORGANIZATION NAME(S) AND ADDRESS(ES) Electron Devices Branch (AFRL/SNDD) Aerospace Components and Subsystems Technology Division Sensors Directorate Air Force Research Laboratory, Air Force Materiel Command Wright-Patterson Air Force Base, OH 45433-7320				(AFRL/MLPSM) 8. PERFORMING ORGANIZATION REPORT NUMBER AFRL-SN-WP-TM-2003-1191		
9. SPONSORING/MONITORING AGENCY NAME(S) AND ADDRESS(ES) Sensors Directorate Air Force Research Laboratory Air Force Materiel Command Wright-Patterson Air Force Base, OH 45433-7320				Air Force Office of Scientific Research 4015 Wilson Blvd. Arlington, VA 22203		
10. SPONSORING/MONITORING AGENCY ACRONYM(S) AFRL/SNDD				11. SPONSORING/MONITORING AGENCY REPORT NUMBER(S) AFRL-SN-WP-TM-2003-1191		
12. DISTRIBUTION/AVAILABILITY STATEMENT Approved for public release; distribution is unlimited.						
13. SUPPLEMENTARY NOTES						
14. ABSTRACT (Maximum 200 Words) This is an interim report on research on vertical external-cavity surface-emitting lasers, a collaboration between AFRL and the University of Arizona. This report investigates heat generation under high-power optical pumping for VECSELs, and studies the effects of sample mounting and substrate removal by means of photoluminescence experiments.						
15. SUBJECT TERMS Diode lasers, laser packaging, opto-electronic materials						
16. SECURITY CLASSIFICATION OF:			17. LIMITATION OF ABSTRACT: SAR		18. NUMBER OF PAGES 10	
a. REPORT Unclassified	b. ABSTRACT Unclassified	c. THIS PAGE Unclassified				
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Heat Dissipation for High Power Optically Pumped Semiconductor Vertical External Cavity Surface Emitting Lasers

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Abstract: We investigate heat generation under high power optical pumping for vertical external cavity surface emitting lasers. The effects of sample mounting and substrate removal on the photoluminescence are investigated. Efficient heat extraction is reported.

Optically pumped semiconductor (OPS) vertical external cavity surface emitting lasers (VECSEL) have a number of advantages over conventional semiconductor diode lasers, such as high brightness and good beam quality [1,2]. High power CW operation of the OPS-VECSEL requires proper thermal design of the structure and efficient heat extraction from the active region to avoid thermal lensing, decreased gain, and shut-off resulting with resonant frequency shifts. In order to achieve this goal, the epitaxial structure should be as close as possible to the heat sink. In addition, mechanical strain caused by the mounting method should be avoided. In this paper we investigate several methods for substrate removal and sample mounting.

The epitaxial structure used consists of 14 strained $\text{In}_{0.15}\text{Ga}_{0.85}\text{As}$ 8nm quantum wells and 129.6 nm wide GaAs barriers. The barrier width is designed to position the quantum wells at the antinodes of the longitudinal standing wave of the VECSEL. For purposes of this test, there is no DBR mirror included in growth. There is an $\text{Al}_{0.8}\text{Ga}_{0.2}\text{As}$ etch-stop grown between the active structure and the substrate to facilitate chemical substrate removal.

The intra-cavity surface is left uncooled, while the heat is to be primarily removed through opposite face. We study three mounting methods: (1) leaving a nominally 650 μm substrate, (2) mounting the epitaxial side of the sample to an AlN submount using a thermal epoxy, completely remove the substrate from opposite side, and (3) the same procedure as method 2, but instead using indium to solder the semiconductor to the AlN submount.

For substrate removal, we first attach the semiconductor to the AlN submount from the epitaxial side. We then mechanically lap the GaAs substrate to a thickness of about 120 μm . The remaining GaAs substrate is subsequently removed by selective wet chemical etching using $\text{C}_6\text{H}_8\text{O}_7\text{:H}_2\text{O}_2$. A single $\lambda/4$ dielectric layer is then applied to the intra-cavity surface using e-beam evaporation. Samples with the entire substrate removed are only about 2 μm in total thickness.

In measurements, all samples are mounted, using thermal grease, to a water-cooled heat sink maintained at 10 °C. We optically excite the material with an 808 nm source incident at 45 degrees, and capture the photoluminescence (PL) in reflection mode from the wafer normal. Pump densities used are commensurate with typical above-threshold pump densities.

In this structure there is no layer compensating the quantum well strain. To investigate mismatch of the coefficient of thermal expansion (CTE) between the quantum wells and the submount, and strain generated by substrate removal, PL curves taken before and substrate removal are compared. Despite the elevated indium processing temperature, the PL line shape remains reasonably consistent before and after substrate removal, indicating no strain relaxation (see Fig. 1a).

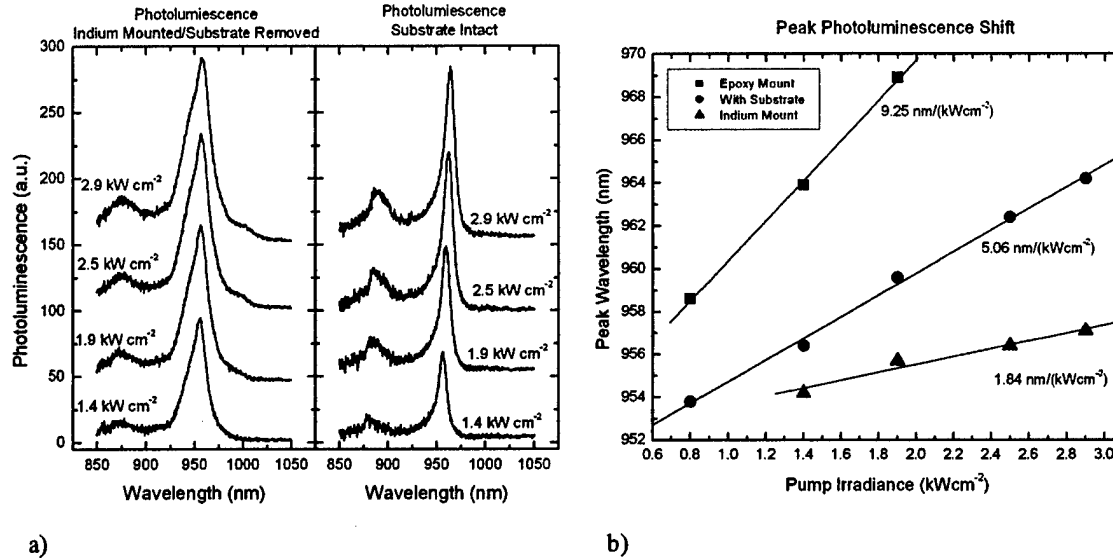


Fig. 1. a) PL result comparing indium solder mounted sample (left) and unprocessed sample (right). b) Peak PL measurement for different mounting methods.

Fig. 1b records the shift in PL as a function of pump irradiance. If the heat is to be removed through the entire substrate, this results in a peak wavelength shift rate of 5 nm/(kW cm⁻²). Assuming a typical wavelength shift of 0.3 nm/°C, this results in a temperature rate of change of about 16 °C/(kW cm⁻²), unacceptably high for efficient VECSEL operation.

There are several advantages using thermal epoxy including low stress, low temperature application, and ease of process. We see however the thermal epoxy is not effective for heat removal (Fig. 1b), with a 31 °C/(kW cm⁻²) temperature rate of change. This is due in part to the relatively low thermal conductivity of the epoxy (~7 W/m/K) relative to the substrate thermal conductivity. Minimum epoxy thickness is on the order of 20 μm, resulting in a significant thermal resistance.

The best results by far are obtained by mounting the sample using indium solder. While this is done at an elevated temperature, there is no additional stress applied to the semiconductor, as indicated by the PL shape (Fig. 1a). The indium solder mounted sample's PL shifts at only about 2 nm/(W cm⁻²), which indicates a temperature rate of change of only 6 °C/(kW cm⁻²). These results will be somewhat depreciated when the distributed Bragg reflector (DBR) stack is grown, as the heat is to be removed *through* the DBR layers.

In comparing mounting methods and processing techniques, we find that indium solder used in conjunction with substrate removal is effective for heat removal from VECSEL material. Future use of CVD diamond should improve heat transfer due to its superior thermal conductivity.

References

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